

40 V, 10 A PNP high power bipolar transistor 21 January 2015

Product data sheet

### 1. General description

PNP high power bipolar transistor in a SOT669 (LFPAK56) Surface-Mounted Device (SMD) power plastic package.

NPN complement: PHPT60410NY

### 2. Features and benefits

- High thermal power dissipation capability
- Suitable for high temperature applications up to 175 °C
- Reduced Printed-Circuit Board (PCB) requirements comparing to transistors in DPAK
  - High energy efficiency due to less heat generation
  - AEC-Q101 qualified

### 3. Applications

- Power management
- Load switch
- Linear mode voltage regulator
- Backlighting applications
- Motor drive
- Relay replacement

### 4. Quick reference data

Table 1.     Quick reference data							
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>CEO</sub>	collector-emitter voltage	open base		-	-	-40	V
I <sub>C</sub>	collector current			-	-	-10	А
I <sub>CM</sub>	peak collector current	$t_p \le 1 \text{ ms}; \text{ single pulse}$		-	-	-20	А
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_C$ = -10 A; $I_B$ = -1 A; pulsed; $t_p$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C		-	37	55	mΩ

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# 5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	E	emitter	mb	С
2	E	emitter		в
3	E	emitter	a	1×
4	В	base	មុច្ចុថ្	sym132
mb	С	collector	1 2 3 4 LFPAK56; Power- SO8 (SOT669)	

# 6. Ordering information

Table 3. Ordering information					
Type number	Package				
	Name	Description	Version		
PHPT60410PY	LFPAK56; Power-SO8	Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads	SOT669		

# 7. Marking

Table 4. Marking codes	
Type number	Marking code
PHPT60410PY	0410PAB

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### 8. Limiting values

#### Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>CBO</sub>	collector-base voltage	open emitter		-	-40	V
V <sub>CEO</sub>	collector-emitter voltage	open base		-	-40	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	-8	V
I <sub>C</sub>	collector current			-	-10	А
I <sub>CM</sub>	peak collector current	$t_p \le 1 \text{ ms}; \text{ single pulse}$		-	-20	А
I <sub>B</sub>	base current			-	-1	А
I <sub>BM</sub>	peak base current	$t_p \le 1 ms; pulsed$		-	-2	А
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	1.3	W
			[2]	-	3.3	W
			[ <u>3]</u>	-	5	W
			[4]	-	25	W
Tj	junction temperature			-	175	°C
T <sub>amb</sub>	ambient temperature			-55	175	°C
T <sub>stg</sub>	storage temperature			-65	175	°C

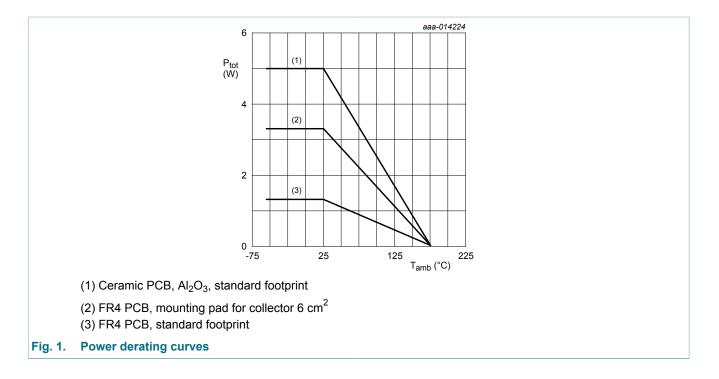
[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated mounting pad for collector 6 cm<sup>2</sup>.

[3] Device mounted on an ceramic Printed-Circuit Board (PCB), Al<sub>2</sub>O<sub>3</sub>, standard footprint.

[4] Power dissipation from junction to mounting base.

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### 9. Thermal characteristics

#### Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
	thermal resistance from junction to ambient	in free air	[1]	-	-	115	K/W
			[2]	-	-	45	K/W
			[3]	-	-	30	K/W
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base			-	-	6	K/W

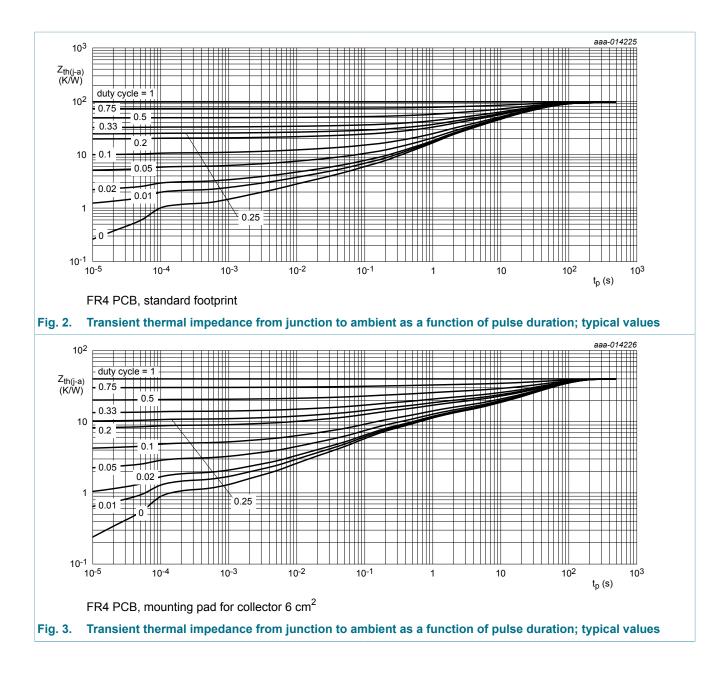
[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard

footprint.
 [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for collector 6 cm<sup>2</sup>.

[3] Device mounted on an ceramic Printed-Circuit Board (PCB), Al<sub>2</sub>O<sub>3</sub>, standard footprint.



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# **10. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
I <sub>CBO</sub>	collector-base cut-off	V <sub>CB</sub> = -32 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	-100	nA
	current	V <sub>CB</sub> = -32 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C	-	-	-50	μA
I <sub>CES</sub>	collector-emitter cut-off current	$V_{CE}$ = -32 V; $V_{BE}$ = 0 V; $T_{amb}$ = 25 °C	-	-	-100	nA
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB}$ = -8 V; I <sub>C</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	-100	nA
h <sub>FE</sub>	DC current gain	$V_{CE}$ = -2 V; I <sub>C</sub> = -500 mA; T <sub>amb</sub> = 25 °C	240	350	-	
		$V_{CE}$ = -2 V; I <sub>C</sub> = -1 A; t <sub>p</sub> ≤ 300 µs; $\bar{\delta} \le 0.02$ ; T <sub>amb</sub> = 25 °C; pulsed	220	320	-	
		$V_{CE} = -2 \text{ V; } I_C = -5 \text{ A; } t_p \le 300  \mu\text{s;}$ $\delta \le 0.02; \text{ T}_{amb} = 25 \text{ °C; pulsed}$	100	150	-	
		$V_{CE}$ = -2 V; I <sub>C</sub> = -10 A; pulsed; t <sub>p</sub> ≤ 300 µs; $\delta$ ≤ 0.02; T <sub>amb</sub> = 25 °C	40	50	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$\begin{split} I_{C} &= -1 \text{ A};  I_{B} = -50 \text{ mA};  t_{p} \leq 300  \mu\text{s}; \\ \delta &\leq 0.02;  T_{amb} = 25 ^{\circ}\text{C} \end{split}$	-	-50	-70	mV
		$I_{C}$ = -5 A; $I_{B}$ = -500 mA; pulsed; $t_{p} \le 300 \ \mu$ s; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-180	-250	mV
		$I_{C}$ = -10 A; $I_{B}$ = -500 mA; pulsed; $t_{p} \le 300 \ \mu$ s; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-550	-800	mV
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_{C}$ = -10 A; $I_{B}$ = -1 A; pulsed; $t_{p} \le 300 \ \mu$ s; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	37	55	mΩ
V <sub>BEsat</sub>	base-emitter saturation voltage	$I_{C}$ = -1 A; $I_{B}$ = -50 mA; pulsed; $t_{p} \le 300 \ \mu$ s; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-	-0.95	V
		$I_{C}$ = -5 A; $I_{B}$ = -500 mA; pulsed; $t_{p} \le 300 \ \mu$ s; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-	-1.15	V
		$I_{C}$ = -10 A; $I_{B}$ = -500 mA; pulsed; $t_{p} \le 300 \ \mu$ s; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-	-1.25	V
V <sub>BEon</sub>	base-emitter turn-on voltage	$V_{CE}$ = -2 V; I <sub>C</sub> = -500 mA; T <sub>amb</sub> = 25 °C	-	-	-0.8	V
t <sub>d</sub>	delay time	V <sub>CC</sub> = -12.5 V; I <sub>C</sub> = -5 A;	-	15	-	ns
t <sub>r</sub>	rise time	I <sub>Bon</sub> = -250 mA; I <sub>Boff</sub> = 250 mA;	-	105	-	ns
t <sub>on</sub>	turn-on time	T <sub>amb</sub> = 25 °C	-	120	-	ns
s	storage time		-	155	-	ns
f	fall time	-	-	80	-	ns
t <sub>off</sub>	turn-off time	-	-	235	-	ns

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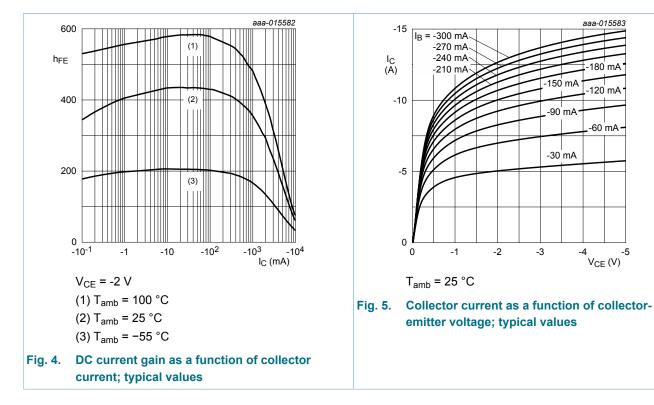
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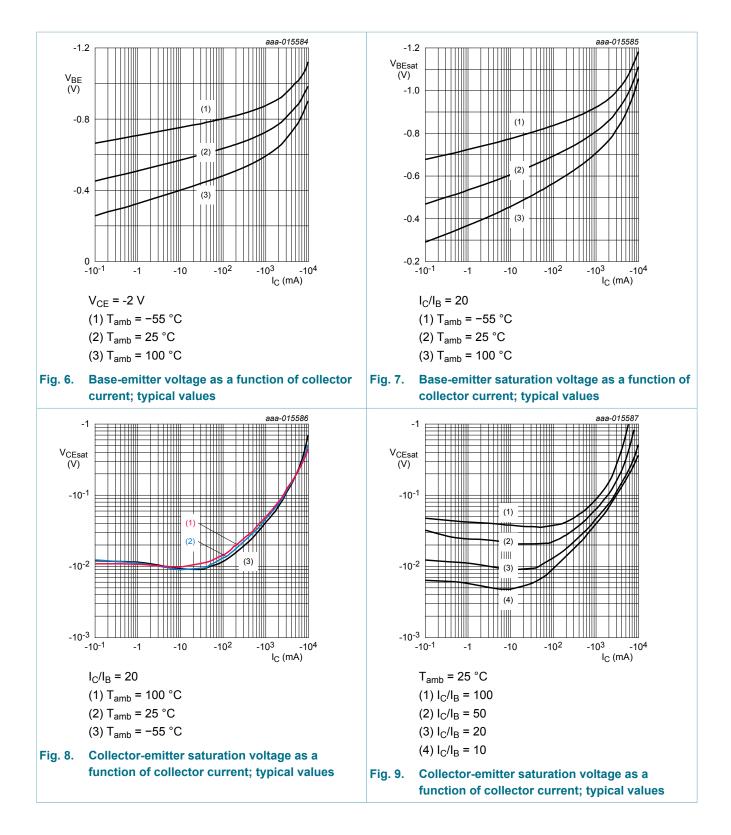
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Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
f <sub>T</sub>	transition frequency	V <sub>CE</sub> = -10 V; I <sub>C</sub> = -500 mA; f = 100 MHz; T <sub>amb</sub> = 25 °C	-	97	-	MHz
C <sub>c</sub>	collector capacitance	V <sub>CB</sub> = -10 V; I <sub>E</sub> = 0 A; i <sub>e</sub> = 0 A; f = 1 MHz; T <sub>amb</sub> = 25 °C	-	84	-	pF



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#### 40 V, 10 A PNP high power bipolar transistor



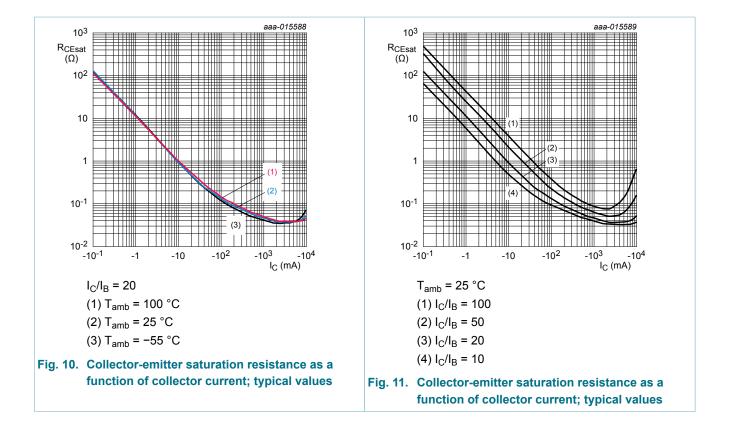
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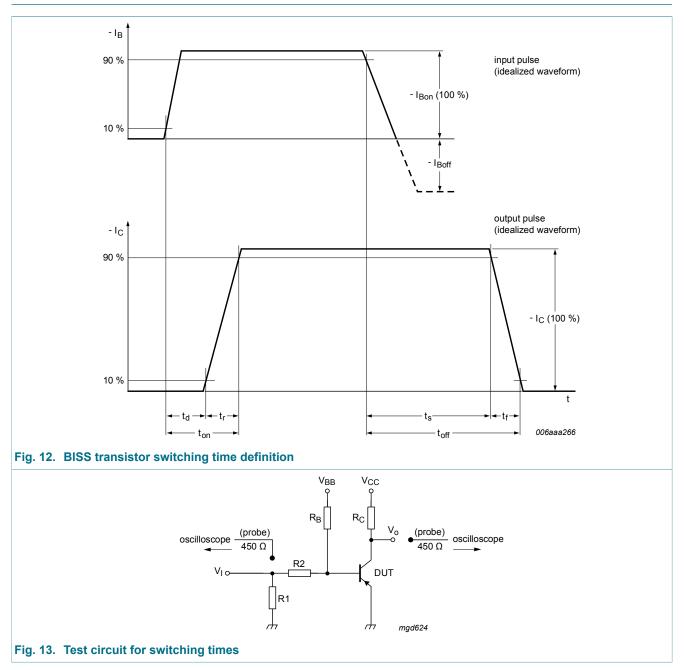
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#### 40 V, 10 A PNP high power bipolar transistor



### **11. Test information**



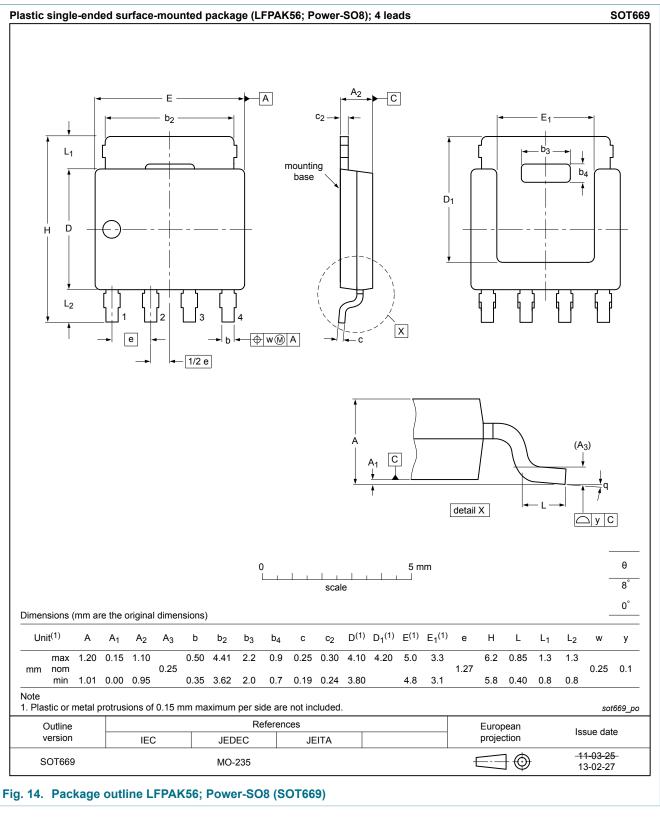
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### 12. Package outline



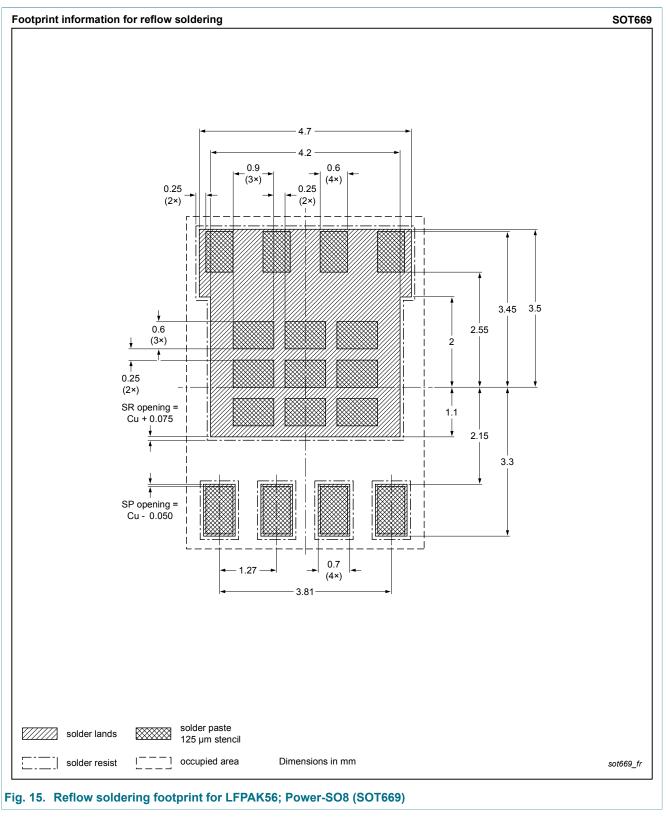
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### 13. Soldering



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#### 40 V, 10 A PNP high power bipolar transistor

# 14. Revision history

Table 8. Revision history						
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes		
PHPT60410PY v.1	20150121	Product data sheet	-	-		

#### 40 V, 10 A PNP high power bipolar transistor

### 15. Legal information

#### 15.1 Data sheet status

Document status [1][2]	Product status [ <u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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